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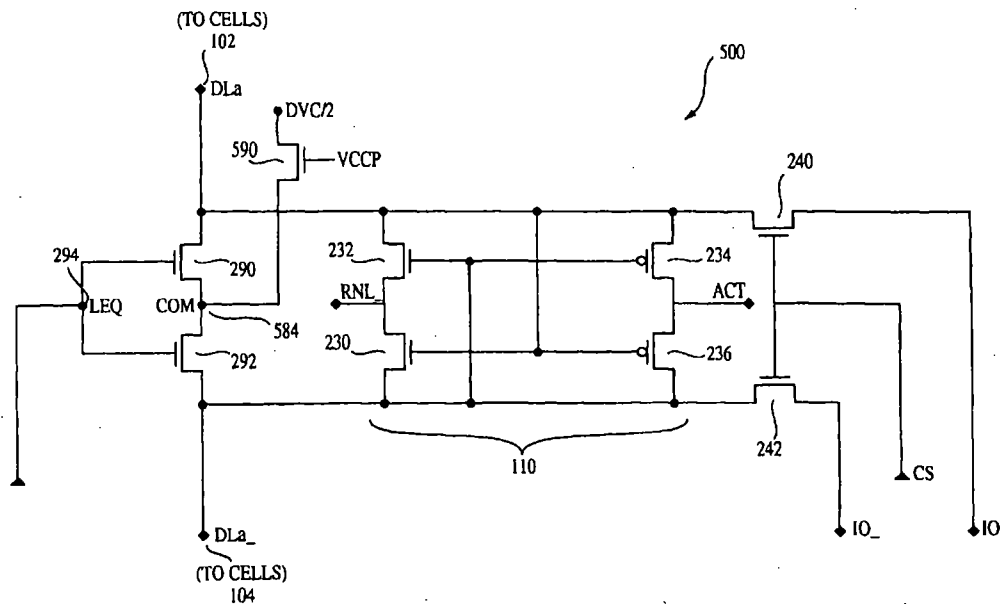
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(54) Title: SENSE AMPLIFIER AND ARCHITECTURE FOR OPEN DIGIT ARRAYS



(57) Abstract: A method and apparatus are described which provide a memory device with sense amplifiers extending in a first direction and corresponding digit lines extending in a second direction perpendicular to the first direction. A pair of complementary digit lines may originate from different memory sub-arrays. The arrangement is particular useful for memory arrays having 6F**2 feature size.

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